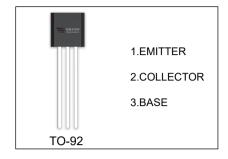


2SD1991A TRANSISTOR (NPN)

FEATURES

- High Foward Current Transfer Ratio h_{FE}
- Low Collector to Emitter Saturation Voltage V_{CE(sat)}.
- Allowing Supply with the Radial Taping.



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SD1991A	TO-92	Bulk	1000pcs/Bag
2SD1991A-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (Ta=25 ℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current -Continuous	100	mA
Pc	Collector Power Dissipation	400	mW
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C



$T_a \text{=} 25\,^\circ\!\!\subset\,$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =10μΑ,I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =2mA,I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA,I _C =0	7			V
Collector cut-off current	I _{CBO}	V _{CB} =20V,I _E =0			1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =7V,I _C =0			1	μA
DC current gain	h _{FE(1)}	V _{CE} =10V,I _C =2mA	160		460	
	h _{FE(2)}	V _{CE} =2V,I _C =100mA	90			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA,I _B =10mA			0.3	V
Transition frequency	f⊤	V _{CE} =10V,I _C =2mA,f=200MHz		150		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V,I _E =0,f=1MHz		3.5		pF

CLASSIFICATION OF h_{FE(1)}

Rank	Q	R	S
Range	160-260	210-340	290-460